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LIGITEK

SINGLE L	DIGIT LED DISPLAY (2.3 Inch)	LSD23	25X/6X series Page 1/2
494 ta - Eraki - Eraka astarrasan dara	PACKAGE DIMENSION		INTERNAL CIRCUIT DIAGRAM
LSD232 LIGIT		60.0 (2.4")	LSD2325X-XX 1 5 F D C B A DP F G A
 Conne 	ction To Electrical Schematic		
	Electrica	al Connecti	ion
PIN NO.	LSD2325X-XX	PIN NO.	LSD2326X-XX
1	Common Cathode	1	Common Anode
2	Anode E	2	Cathode E
3	Anode D	3	Cathode D
4	Anode C	4	Cathode C
5	Common Cathode	5	Common Anode
6	Anode B	6	Cathode B
7	Anode A	7	Cathode A
8	Anode DP	8	Cathode DP
9	Anode F	9	Cathode F
10	Anode G	10	Cathode G
文件纪录	梵∶QW0905-S2325/6X-XX	版本:A	生效日期:Jun.8.1996

	GIT LED DIS		•			ation				5/6X		eries mbie			age 2/
		-144	cau	· · · · · ·					-		······				
PART NO	CHIP			common cathode		λP (nm)	Δλ (nm)		Elect				і∨-м		
				or anode		()				Vf(v)	Max		ncd)		
LSD23255-XX	material GaAlAs	emitted Red				66	0	0 20		<i>Min</i> 1.5	<i>Тур</i> .	2.4	<i>Min</i> 12	Тур . 21	2:1
_SD23251-XX	GaP	Re		- Common _ Cathode		69		<u></u> 90		1.3 1.7	$\frac{1.1}{2.1}$	2.4	4.8	8.0	2:1 2:1 2:1 2:1
LSD23252-XX	GaP	Gre				56		30		1.7	2.1	2.8	9.6	16	
LSD23253-XX	GaAsP/GaP	Yel				58		35		1.7	2.0	2.8	8.4	14	
LSD23254-XX	GaAsP/GaP	Ora				63		45		1.7	2.0	2.8	9.6	16	2:1
LSD23265-XX	GaAlAs	Re				66		20		1.5	1.7	2.4	12	21	2:1
LSD23261-XX	GaP	R	ed			69		90		1.7	2.1	2.8	4.8	8.0	2:1
LSD23262-XX	GaP	Gre		- Common _ Anode		56		30		1.7	2.1	2.8	9.6	16	2:1
LSD23263-XX	GaAsP/GaP	Yel	ow			58		35		1.7	2.0	2.8	8.4	14	2:1
LSD23264-XX	GaAsP/GaP	Orange		1			5	45		1.7	2.0	2.8	9.6	16	2:1
Absolute	Maximum Ra	ting	(Ta=	=25°C	;)	L				L	L	I		L	L
Parameter			Red Gre		en Yellow			Orange		Unit		Remark			
Forward Current Per Chip		SR		н		G		Y			E				
		40		15		30		20			30	n	۱A	1	
Peak Current Per Chip (Duty 1/10, 0.1MS Pulse Width)		200		60		120		80			120	n	hΑ		
Power Dissipation Per Chip		1	0	45 100		0	85		100		mW				
Derating Linear From 25°C Per Chip		0.	45	0.25 0.45		5 0.45		0.45		mA/ °C					
Reverse Current Per Any Chip			10) 10		10		10		μΑ					
Operating Temperature				-25°C TO +85°C											
Storage Temperature				-25°C TO +85°C											
Solder Tempera	ature 1/16 Inch B	elow S	eatir	ig Plan	e For 3	Seco	nds /	\t 260 ⁰	C						
Test Con	dition For Ea	ch Pa	aran	neter											
Parameter						Symbol			Unit		Test Condition				
Forward Voltage Per Chip						Vf			volt		lf=20mA				
Luminous Intensity Per Chip					Iv			mcd		lf=10mA					
Peak Emission Wavelength					λρ			nm		lf=20mA					
Spectral Line Half-Width					Δλ			nm		lf=20mA					
Reverse Current Any Chip						Ir			μA		Vr=5V		=5V		
Luminous Intensity Matching Ratio							IV-I					1			